Masayuki Imanishi

List of Publications by Year
in descending order

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41 papers	519 citations	759233 12 h-index	713466 21 g-index
41 all docs	41 docs citations	41 times ranked	348 citing authors

#	Article	IF	Citations
1	Fabrication of low-curvature 2 in. GaN wafers by Na-flux coalescence growth technique. Applied Physics Express, 2014, 7, 035503.	2.4	65
2	Recent progress of Na-flux method for GaN crystal growth. Japanese Journal of Applied Physics, 2019, 58, SC0803.	1.5	48
3	Homoepitaxial Hydride Vapor Phase Epitaxy Growth on GaN Wafers Manufactured by the Na-Flux Method. Crystal Growth and Design, 2017, 17, 3806-3811.	3.0	45
4	Dramatic reduction of dislocations on a GaN point seed crystal by coalescence of bunched steps during Na-flux growth. Journal of Crystal Growth, 2015, 427, 87-93.	1.5	42
5	Terahertz time-domain ellipsometry with high precision for the evaluation of GaN crystals with carrier densities up to 1020Âcmâ˜3. Scientific Reports, 2021, 11, 18129.	3.3	37
6	Promotion of lateral growth of GaN crystals on point seeds by extraction of substrates from melt in the Na-flux method. Applied Physics Express, 2019, 12, 045508.	2.4	33
7	Thermal conductivity of GaN single crystals: Influence of impurities incorporated in different growth processes. Journal of Applied Physics, 2018, 124, .	2.5	25
8	Vacancy-type defects in bulk GaN grown by the Na-flux method probed using positron annihilation. Journal of Crystal Growth, 2017, 475, 261-265.	1.5	15
9	Crystallization of aspirin form II by femtosecond laser irradiation. Applied Physics Express, 2019, 12, 015507.	2.4	15
10	Development of GaN substrate with a large diameter and small orientation deviation. Physica Status Solidi (B): Basic Research, 2017, 254, 1600671.	1.5	14
11	Extreme reduction of on-resistance in vertical GaN pâ€“n diodes by low dislocation density and high carrier concentration GaN wafers fabricated using oxide vapor phase epitaxy method. Applied Physics Express, 2020, 13, 071010.	2.4	14
12	Homoepitaxial growth of GaN crystals by Na-flux dipping method. Japanese Journal of Applied Physics, 2015, 54, 105501.	1.5	13
13	Enhancement of lateral growth of the GaN crystal with extremely low dislocation density during the Na-flux growth on a point seed. Journal of Crystal Growth, 2017, 468, 827-830.	1.5	13
14	Correlation between current leakage and structural properties of threading dislocations in GaN bulk single crystals grown using a Na-flux method. Japanese Journal of Applied Physics, 2019, 58, SCCB23.	1.5	13
15	Growth of high-quality metastable crystal of acetaminophen using solution-mediated phase transformation at low supersaturation. Journal of Crystal Growth, 2018, 502, 76-82.	1.5	12
16	Habit control during growth on GaN point seed crystals by Na-flux method. Japanese Journal of Applied Physics, 2017, 56, 01AD01.	1.5	10
17	Absolute surface energies of oxygen-adsorbed GaN surfaces. Journal of Crystal Growth, 2020, 549, 125868.	1.5	10
18	Increase in the growth rate of GaN crystals by using gaseous methane in the Na flux method. Japanese Journal of Applied Physics, 2017, 56, 055502.	1.5	9

#	Article	IF	Citations
19	Identification of Burgers vectors of threading dislocations in freestanding GaN substrates via multiphoton-excitation photoluminescence mapping. Applied Physics Express, 2021, 14, 055504.	2.4	9
20	Intergrowth of two aspirin polymorphism observed with Raman spectroscopy. Journal of Crystal Growth, 2020, 532, 125430.	1.5	8
21	Effect of methane additive on GaN growth using the OVPE method. Japanese Journal of Applied Physics, 2019, 58, SC1021.	1.5	7
22	Anomalous dislocation annihilation behavior observed in a GaN crystal grown on point seeds by the Na-flux method. Applied Physics Express, 2020, 13, 085510.	2.4	7
23	Crack-free GaN substrates grown by the Na-flux method with a sapphire dissolution technique. Applied Physics Express, 2016, 9, 071002.	2.4	6
24	Effect of flux composition ratio on the coalescence growth of GaN crystals by the Na-flux method. Optical Materials, 2017, 65, 38-41.	3.6	5
25	Growth of GaN single crystals with high transparency by the Li-added Na-flux method. Journal of Crystal Growth, 2020, 535, 125478.	1.5	5
26	Effects of Al additives on growth of GaN polycrystals by the Na flux method. Optical Materials, 2017, 65, 42-45.	3.6	4
27	Monitoring of Ga-Na melt electrical resistance and its correlation with crystal growth on the Na Flux method. Applied Physics Express, 2019, 12, 065502.	2.4	4
28	Quantitative analysis of lattice plane microstructure in the growth direction of a modified Na-flux GaN crystal using nanobeam X-ray diffraction. Japanese Journal of Applied Physics, 2019, 58, SCCB16.	1.5	4
29	Local current leakage at threading dislocations in GaN bulk single crystals grown by a modified Na-flux method. Japanese Journal of Applied Physics, 2019, 58, 050918.	1.5	4
30	Floral design GaN crystals: low-resistive and low-dislocation-density growth by oxide vapor phase epitaxy. Japanese Journal of Applied Physics, 2021, 60, 095501.	1.5	4
31	Growth of GaN layers using Ga2O vapor synthesized from Ga2O3 and carbon. Journal of Crystal Growth, 2020, 535, 125524.	1.5	3
32	Temperature dependence of nitrogen dissolution on Na flux growth. Journal of Crystal Growth, 2020, 535, 125549.	1.5	3
33	Fabrication of a 1.5-inch freestanding GaN substrate by selective dissolution of sapphire using Li after the Na-flux growth. Journal of Crystal Growth, 2020, 533, 125462.	1.5	2
34	Influence of GaN/sapphire contact area on bowing of GaN wafer grown by the Na-flux method with a sapphire dissolution process. Japanese Journal of Applied Physics, 2020, 59, 025505.	1.5	2
35	Fabrication of GaN crystals with low threading dislocation density and low resistivity by thin flux growth in the Na-flux point seed technique. Japanese Journal of Applied Physics, 2020, 59, 035501.	1.5	2
36	High-rate OVPE-GaN growth by the suppression of polycrystal formation with additional H₂O vapor in a high-temperature condition. Applied Physics Express, 2020, 13, 095504.	2.4	2

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37	Effect of additional N2O gas on the suppression of polycrystal formation and high-rate GaN crystal growth by OVPE method. Journal of Crystal Growth, 2022, 581, 126495.	1.5	2
38	Growth of Acetaminophen Polymorphic Crystals and Solution-Mediated Phase Transition from Trihydrate to Form II in Agarose Gel. Crystals, 2021, 11, 1069.	2.2	1
39	Suppression of newly generated threading dislocations at the regrowth interface of a GaN crystal by growth rate control in the Na-flux method. Japanese Journal of Applied Physics, 0, , .	1.5	1
40	Influence of oxygen-related defects on the electronic structure of GaN. Japanese Journal of Applied Physics, 2022, 61, 061004.	1.5	1
41	Growth of a High Quality GaN Wafer from Point Seeds by the Na-Flux Method. , 2021, , .		0